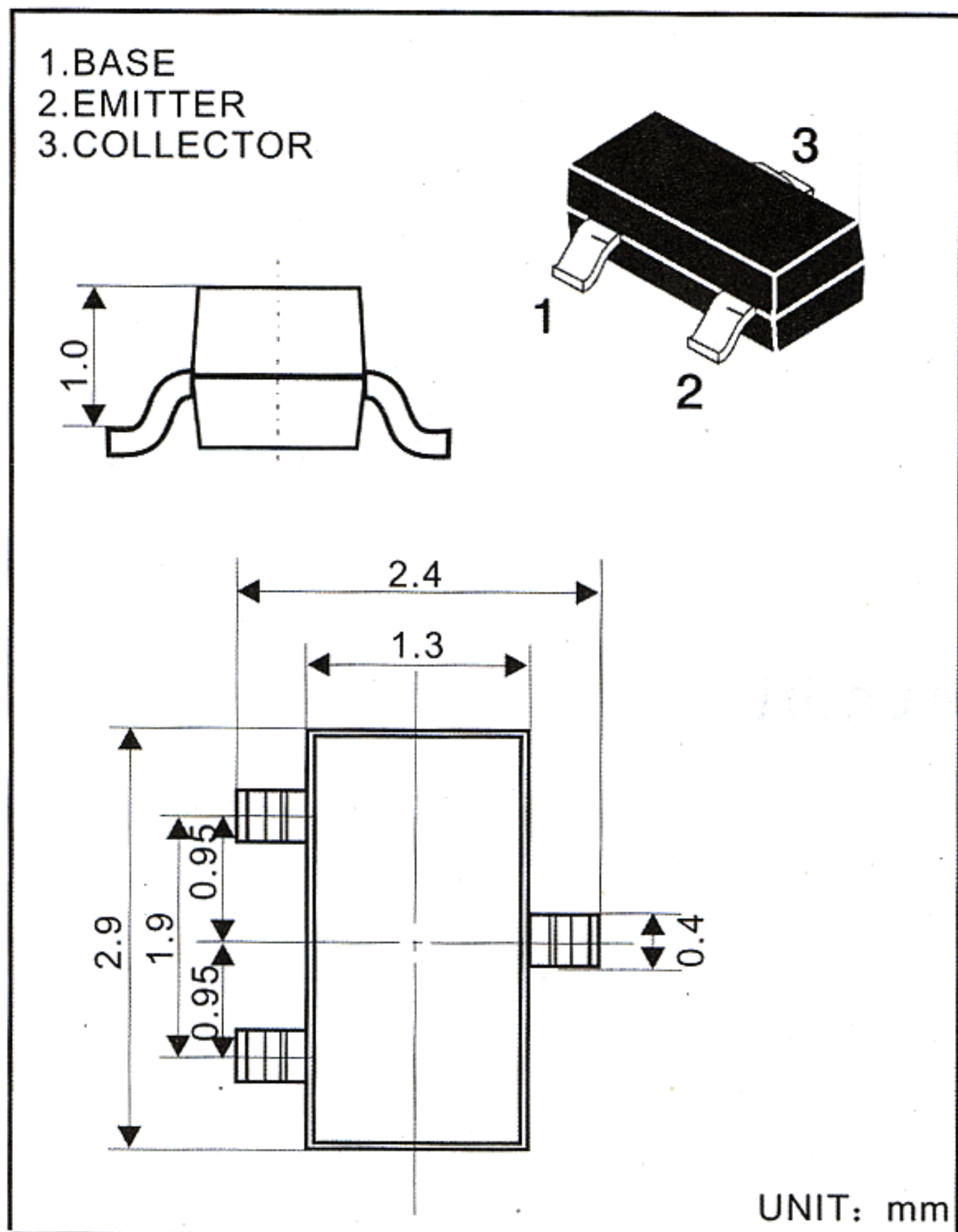


# SOT-23 Plastic-Encapsulate Transistors

## 2SC1623 TRANSISTOR (NPN)



### FEATURES

#### Power dissipation

$P_{CM}$ : 0.2 W ( $T_{amb}=25^{\circ}C$ )

#### Collector current

$I_{CM}$ : 0.1A

#### Collector-base voltage

$V_{(BR)CBO}$ : 60V

#### Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

### ELECTRICAL CHARACTERISTICS

( $T_{amp}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_B=0$	5		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60V, I_E=0$		0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$		0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=6V, I_C=1mA$	90	600	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C=100mA, I_B=5mA$		0.3	V
Base-emitter saturation voltage	$V_{BEsat}$	$I_C=100mA, I_B=5mA$		1	V
Base-emitter voltage	$V_{BEF}$	$V_{CE}=6V, I_E=10mA$	0.55	0.65	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=1mA$	250		MHz

### CLASSIFICATION OF $h_{FE}$

RANK	L4	L5	L6	L7
RANGE	90-180	135-270	200-400	300-600